

# Raymond T Tung

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/7038976/publications.pdf>

Version: 2024-02-01

20  
papers

2,927  
citations

840776

11  
h-index

794594

19  
g-index

20  
all docs

20  
docs citations

20  
times ranked

3907  
citing authors

#	ARTICLE	IF	CITATIONS
1	Recent advances in Schottky barrier concepts. <i>Materials Science and Engineering Reports</i> , 2001, 35, 1-138.	31.8	1,041
2	The physics and chemistry of the Schottky barrier height. <i>Applied Physics Reviews</i> , 2014, 1, .	11.3	931
3	Chemical Bonding and Fermi Level Pinning at Metal-Semiconductor Interfaces. <i>Physical Review Letters</i> , 2000, 84, 6078-6081.	7.8	346
4	Formation of an electric dipole at metal-semiconductor interfaces. <i>Physical Review B</i> , 2001, 64, .	3.2	275
5	Controlling Semiconductor/Metal Junction Barriers by Incomplete, Nonideal Molecular Monolayers. <i>Journal of the American Chemical Society</i> , 2006, 128, 6854-6869.	13.7	102
6	Tuning the Electrical Properties of Si Nanowire Field-Effect Transistors by Molecular Engineering. <i>Small</i> , 2009, 5, 2761-2769.	10.0	80
7	Controlling Au/n-GaAs junctions by partial molecular monolayers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2006, 203, 3438-3451.	1.8	26
8	Charge Density and Band Offsets at Heterovalent Semiconductor Interfaces. <i>Advanced Theory and Simulations</i> , 2018, 1, 1700001.	2.8	20
9	Band offset formation at semiconductor heterojunctions through density-based minimization of interface energy. <i>Physical Review B</i> , 2016, 94, .	3.2	17
10	Controlled modification of Schottky barrier height by partisan interlayer. <i>Solid State Communications</i> , 2011, 151, 1641-1644.	1.9	14
11	Inhomogeneous ohmic contacts: Barrier height and contact area determination. <i>Applied Physics Letters</i> , 2012, 101, 051604.	3.3	12
12	Effect of metal interaction on the Schottky barrier height on adsorbate-terminated silicon surfaces. <i>Applied Surface Science</i> , 2013, 284, 720-725.	6.1	11
13	Schottky barrier height systematics studied by partisan interlayer. <i>Thin Solid Films</i> , 2014, 557, 254-257.	1.8	10
14	Quantitative explanation of the Schottky barrier height. <i>Physical Review B</i> , 2021, 103, .	3.2	10
15	Bidirectional Control of Silicon's Surface Potential by Means of Molecular Coverage. <i>Journal of Physical Chemistry C</i> , 2010, 114, 18674-18678.	3.1	9
16	Bulklike band-offset mystery solved through energy minimization: Lessons from perovskite oxide heterojunctions. <i>Physical Review B</i> , 2019, 99, .	3.2	8
17	Modification of Schottky barrier height on Si (111) by Ga-termination. <i>Surface Science</i> , 2013, 610, 48-52.	1.9	7
18	Fermi level pinning for zinc-blende semiconductors explained with interface bonds. <i>Physical Review B</i> , 2021, 103, .	3.2	7

#	ARTICLE	IF	CITATIONS
19	From NiSi <sub>2</sub> experiments to density functional theory calculations: How the Schottky barrier mystery was solved. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2021, 39, .	2.1	1
20	Combined UHV and Liquid Phase (CULP) Processing of Self-assembled Nanostructures. <i>Materials Research Society Symposia Proceedings</i> , 2005, 879, 1.	0.1	0